

Feng Chia University

Electrical Engineering Fundamentals II Lab

Laboratory 9

BJT- Basic Characteristics and Biasing Circuits

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I. Introduction

- a. To observe the behavior of BJT Basic Characteristics and Biasing Circuits

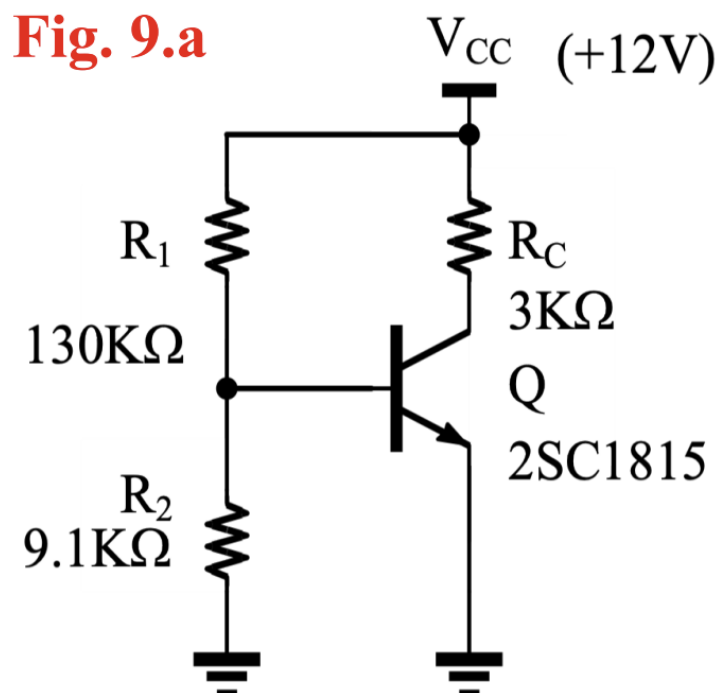
II. Materials

1. Power supply
2. Digital Multimeter
3. Devices

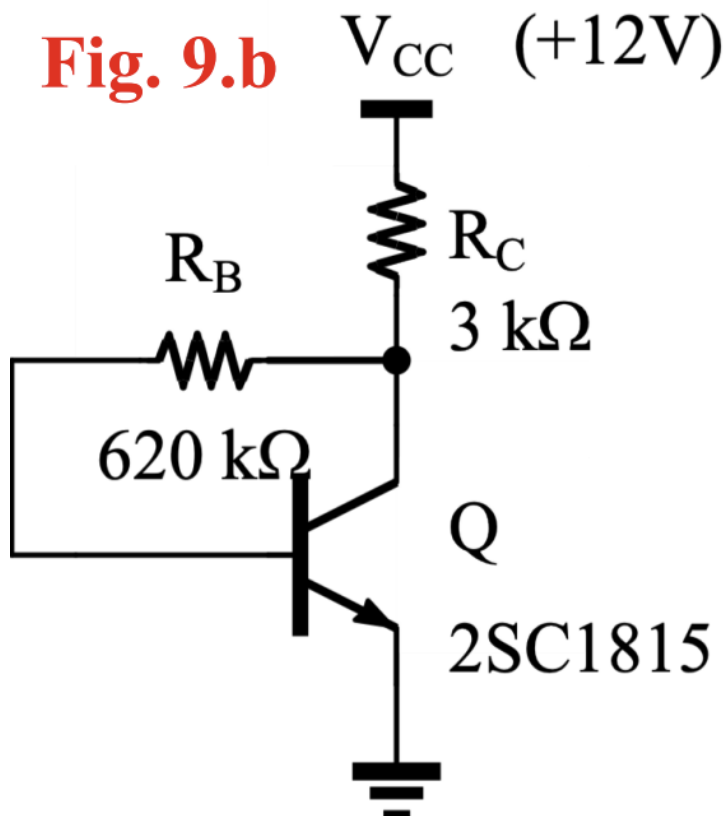
Q: 2SC1815 $\times 1$, 2SC1384 $\times 1$

Resistors: $R = 1\text{ k}\Omega \times 1$, $2.4\text{ k}\Omega \times 1$, $3\text{ k}\Omega \times 1$, $9.1\text{ k}\Omega \times 1$, $15\text{ k}\Omega \times 1$,
 $47\text{ k}\Omega \times 1$, $130\text{ k}\Omega \times 1$, $620\text{ k}\Omega \times 1$

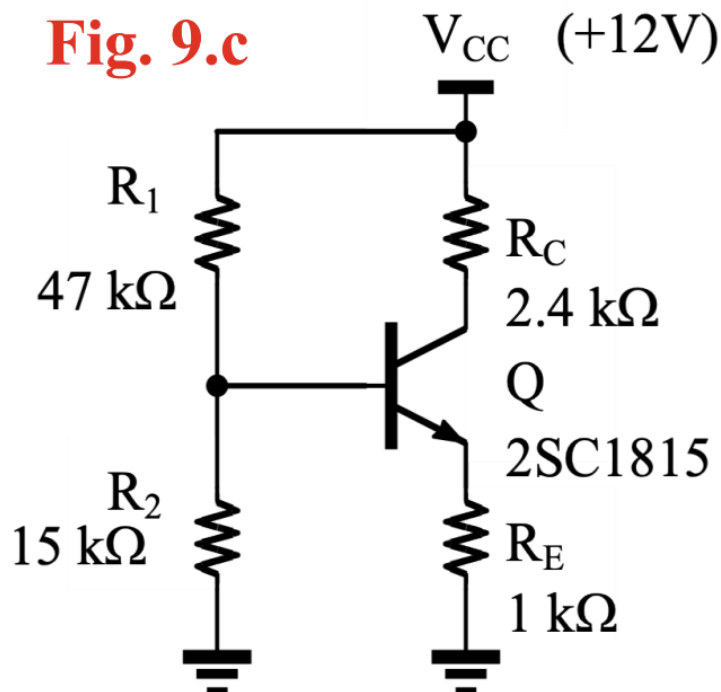
III. Circuit diagram



▲ Figure 1. Circuit of Experiment 9.a Fixing Bias



▲ Figure 2. Circuit of Experiment 9.b Collector-to-Base Feedback



▲ Figure 3. Circuit of Experiment 9.c Negative Feedback with Emitter Resistor

IV. Methods

Using Digital Multimeter to observe voltage and current.

V. Experiments data

1. Experiment 9.a Fixing Bias

Table 1: Measurement of BJT with Fixing Bias

Q	B	B Measure	I _C	I _B	V _{CB}	V _{BE}
1815	309	202.9340	3.9978 mA	0.0197 mA	-0.5148 V	0.6789 V
1384	221	156.4883	4.0061 mA	0.0256 mA	0.0721 V	0.0689 V

2. Experiment 9.b Collector-to-Base Feedback

Table 2: Measurement of Collector-to-Base Feedback

Q	B	B Measure	I _C	I _B	V _{CB}	V _{BE}
1815	309	240.2857	2.0184 mA	0.0084 mA	5.3802 V	0.6279 V
1384	221	198.1290	1.8426 mA	0.0093 mA	5.9146 V	0.6060 V

3. Experiment 9.c Negative Feedback with Emitter Resistor

Table 3: Measurement of Negative Feedback with Emitter Resistor

Q	B	B Measure	I _C	I _B	V _{CB}	V _{BE}
1815	309	295.4865	2.1866 mA	0.0074 mA	4.4462 V	0.6536 V
1384	221	186.2564	2.1792 mA	0.0117 mA	4.5018 V	0.6101 V

VI. Results

None

VII. Discussion

Different BJTs result in different B.

VIII. Conclusion

From the experimental data above, the BJT work in an ideal situation.